

**REMARKS**

The Examiner objected to claims 3-5 as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The Examiner allowed claims 7-20.

Applicants gratefully acknowledge the Examiner's indication of allowable subject matter.

The Examiner rejected claims 1, 2 and 6 under 35 U.S.C. §102(b) as allegedly being anticipated by U.S. Patent No. 6,127,241 to Rha.

Applicants respectfully traverse the §102(b) rejections with the following arguments.

35 U.S.C. §102(b)

The Examiner rejected claims 1, 2 and 6 under 35 U.S.C. §102(b) as allegedly being anticipated by U.S. Patent No. 6,127,241 to Rha.

Applicants respectfully contend that Rha does not anticipate claim 1, because Rha does not teach each and every feature of claim 1. For example, Rha does not teach or suggest "a bubble-implanted semiconductor region" of claim 1.

In bullet #2 of the Office Action, the Examiner alleges that the region 26 of FIG. 2A in Rha teaches the "bubble-implanted semiconductor region" of claim 1. However, Rha in column 4, lines 58-67 and in column 5, lines 1-2 states that "As the wafer is furnace-annealed at a temperature of at least 400°C. (preferably between 400°C. and 450°C.) in an oxidizing ambient, the oxidizing species (O<sub>2</sub> in a dry oxidation process, H<sub>2</sub>O in a wet oxidation process) diffuses through the permeable insulating layer 37 and *reacts with carbon of the etched amorphous carbon layers 36a to form carbon dioxide (CO<sub>2</sub>) gas 36b.* The end point of the oxidation reaction within the cavity (i.e., the point at which the carbon of the etched amorphous carbon layers 36a may be safely assumed to have been *completely converted into gaseous carbon dioxide*) is monitored by means of oxide growth on a test strip on the substrate." (italic emphasis added). In other words, Rha teaches that the region 26 of FIG. 2A contains only gas (carbon dioxide) whereas the "bubble-implanted semiconductor region" of claim 1 contains a solid semiconductor material and bubbles. As a result, Rha does not teach the feature "a bubble-implanted semiconductor region" of claim 1.

Based on the preceding arguments, Applicants respectfully maintain that Rha does not anticipate claim 1, and that claim 1 is in condition for allowance. Since claims 2 and 6 depend

from claim 1, Applicants contend that claims 2 and 6 are likewise in condition for allowance.

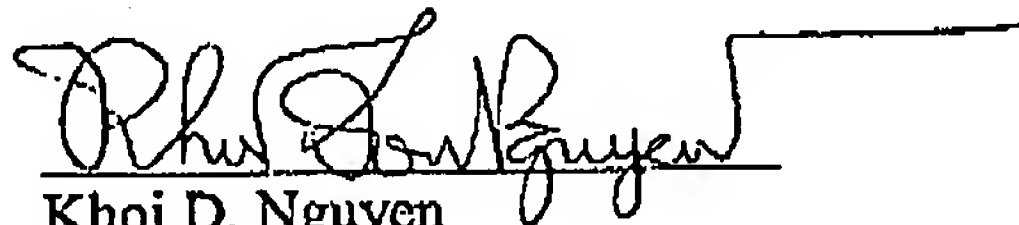
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**CONCLUSION**

Based on the preceding arguments, Applicants respectfully believe that all pending claims and the entire application meet the acceptance criteria for allowance and therefore request favorable action. If the Examiner believes that anything further would be helpful to place the application in better condition for allowance, Applicants invites the Examiner to contact Applicants' representative at the telephone number listed below. The Director is hereby authorized to charge and/or credit Deposit Account 09-0456.

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